

Features :

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

| V _{DSM} , V _{RSM} | V _{DRM} , V _{RRM} | Type & Outline |
|-------------------------------------|-------------------------------------|------------------|
| 2100V | 2000V | MTx1000-20-411F3 |
| 2300V | 2200V | MTx1000-22-411F3 |
| 2600V | 2500V | MTx1000-25-411F3 |

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | T _j (°C) | VALUE | | | UNIT |
|--------------------------------------|--|--|---------------------|-------|------|-------|----------------------------------|
| | | | | Min | Type | Max | |
| I _{T(AV)} | Mean on-state current | 180° half sine wave 50Hz Single side water cooled, T _c =55°C | 125 | | | 1000 | A |
| I _{T(RMS)} | RMS on-state current | | | | | 1570 | A |
| I _{DRM} I _{RRM} | Repetitive peak current | at V _{DRM} at V _{RRM} | 125 | | | 50 | mA |
| I _{TSM} | Surge on-state current | 10ms half sine wave | 125 | | | 18.0 | kA |
| I ² t | I ² t for fusing coordination | V _R =60%V _{RRM} | | | | 1620 | A ² s*10 ³ |
| V _{TO} | Threshold voltage | | 125 | | | 0.85 | V |
| r _T | On-state slope resistance | | | | | 0.20 | mΩ |
| V _{TM} | Peak on-state voltage | I _{TM} =3000A | 25 | | | 2.35 | V |
| dv/dt | Critical rate of rise of off-state voltage | V _{DM} =67%V _{DRM} | 125 | | | 800 | V/μs |
| di/dt | Critical rate of rise of on-state current | Gate source 1.5A t _r ≤ 0.5μs Repetitive | 125 | | | 100 | A/μs |
| I _{GT} | Gate trigger current | V _A =12V, I _A =1A | 25 | 30 | | 200 | mA |
| V _{GT} | Gate trigger voltage | | | 0.8 | | 3.0 | V |
| I _H | Holding current | | | 10 | | 200 | mA |
| V _{GD} | Non-trigger gate voltage | V _{DM} =67%V _{DRM} | 125 | 0.2 | | | V |
| R _{th(j-c)} | Thermal resistance Junction to case | Single side cooled per chip | | | | 0.052 | °C /W |
| R _{th(c-h)} | Thermal resistance case to heat sink | Single side cooled per chip | | | | 0.024 | °C /W |
| V _{iso} | Isolation voltage | 50Hz, R.M.S, t=1min, I _{iso} : 1mA(MAX) | | 3000 | | | V |
| F _m | Terminal connection torque(M12) | | | | 14 | | N·m |
| | Mounting torque(M8) | | | | 12 | | N·m |
| T _{vj} | Junction temperature | | | -40 | | 125 | °C |
| T _{stg} | Stored temperature | | | -40 | | 125 | °C |
| W _t | Weight | | | | 3460 | | g |
| Outline | 411F3 | | | | | | |

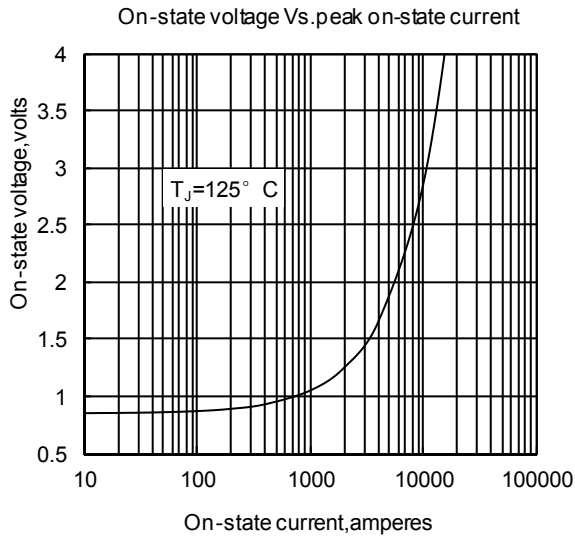


Fig. 1

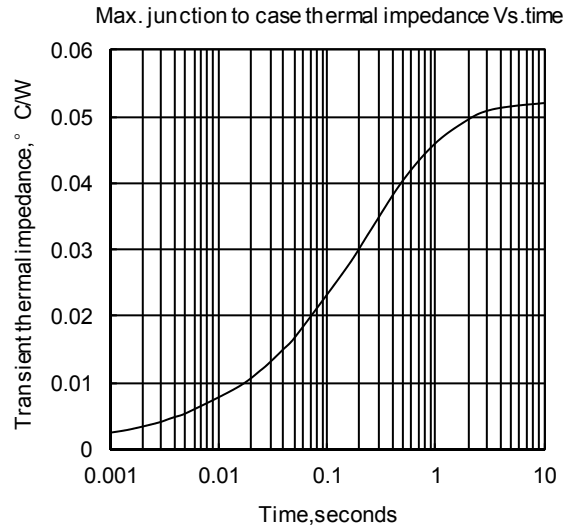


Fig. 2

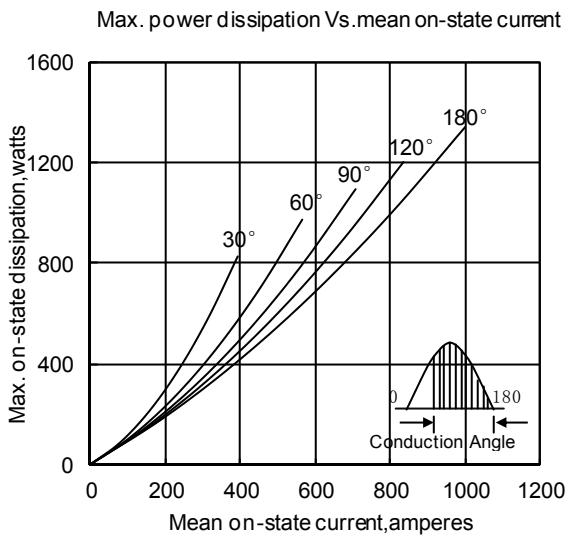


Fig. 3

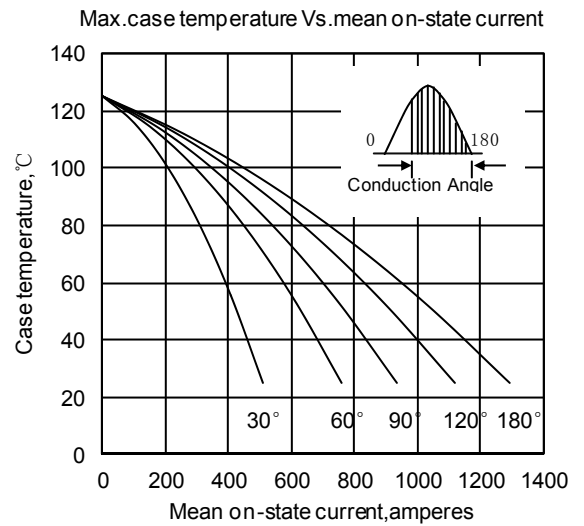


Fig. 4

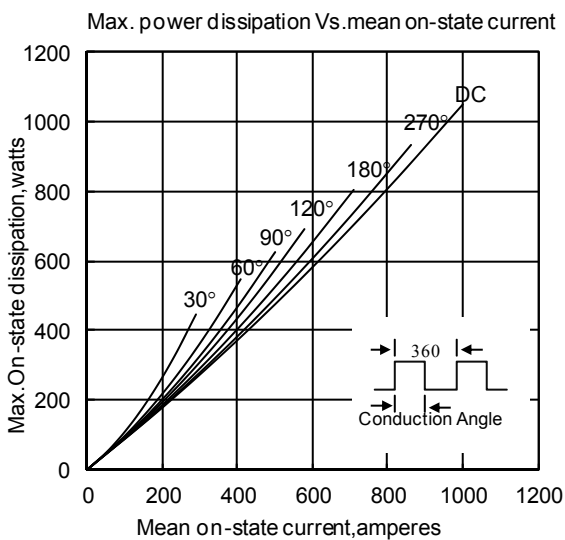


Fig. 5

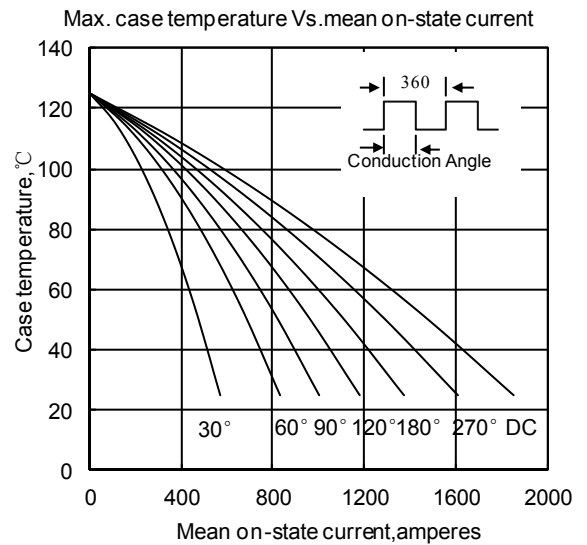


Fig. 6

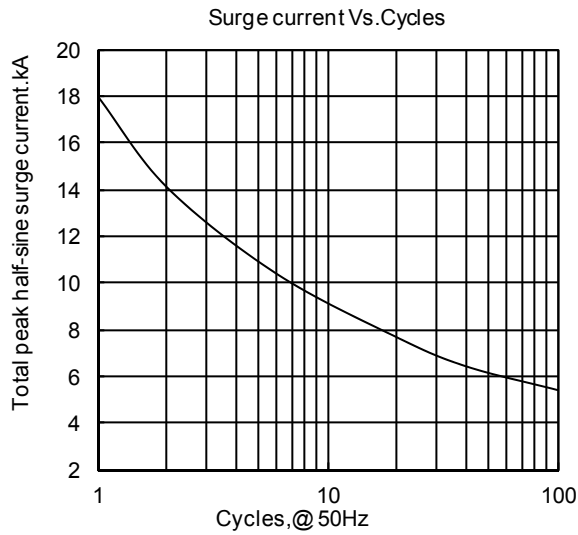


Fig. 7

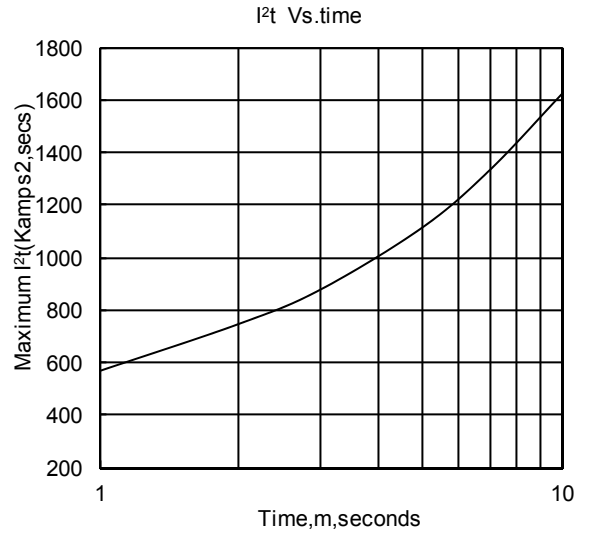


Fig. 8

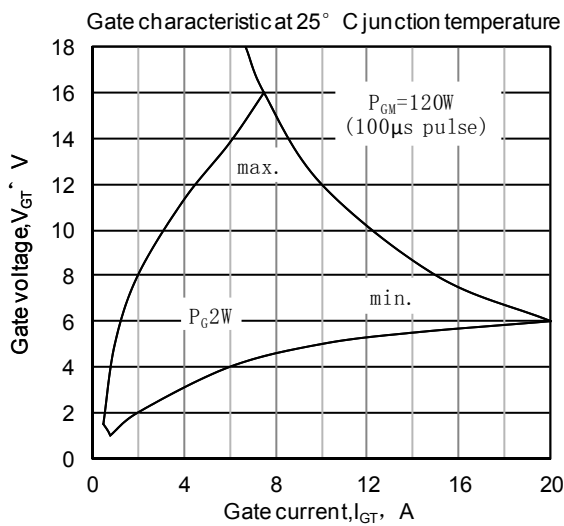


Fig. 9

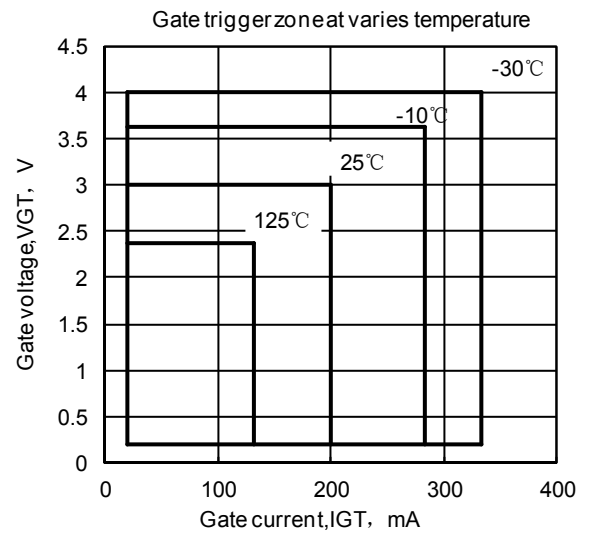


Fig. 10

Outline:

